IR Laser Diode

Application

Industrial use / Biomedical

Property

Wavelength λ = 980nm

Output Power = 100mW

Package Type = φ 5.6mm

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

IR Laser Diode Key features

Absolute Maximum Rating at Tc=25℃			
Items	**Symbols**	**Values**	**Unit**
Optical Output Power	Po(CW)	100	mW
Reverse Voltage	V	2	V
Operating Temperature	To	-10~+40	℃
Storage Temperature	Ts	-10~+70	℃

Electrical and Optical Characteristics at Tc=25℃						
Item	**Symbols**	**Min**	**Typ.**	**Max.**	**Unit**	**Condition**
Optical Output Power	Po	-	-	100	mW	-
Threshold Current	Ith		40	50	mA	-
Operating Current	Iop		165	195	mA	Po=100mW
Operating Voltage	Vop	1	1.5	2.1	V	Po=100mW
Peak Wavelength	λ p	970	980	990	nm	Po=100mW

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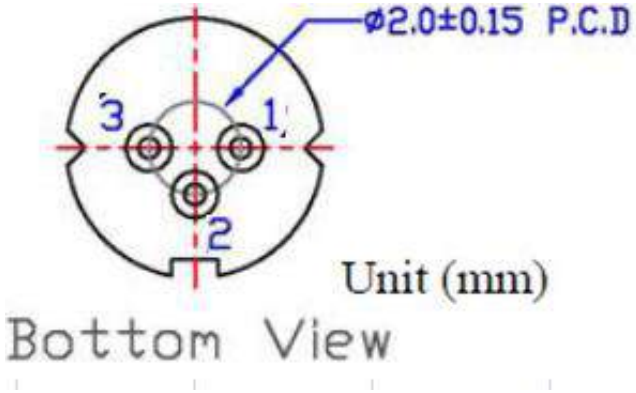
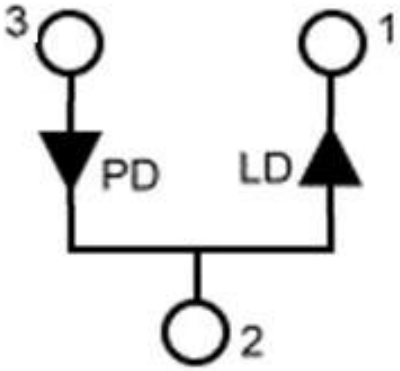
Beam Divergence	θ//	-	6	-	deg	Po=100mW
	θ⊥	27	32	37	deg	Po=100mW

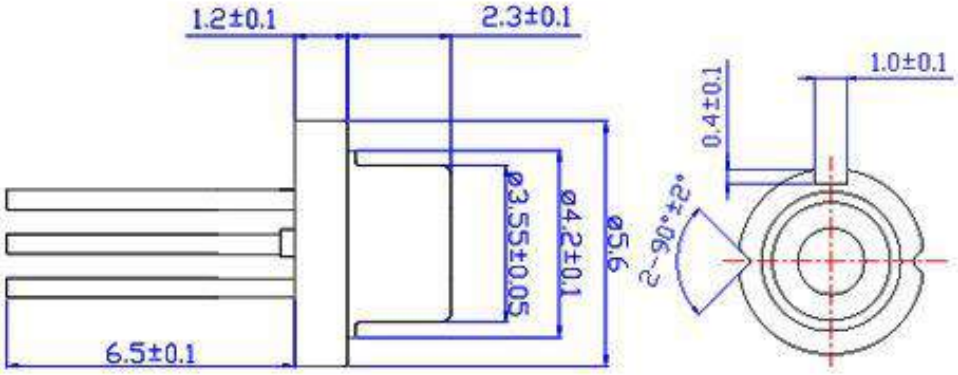
Electrical Connection(Bottom View)



Package Type



Package Drawing



Specifications are subject to change without notice.

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